Supplementary Information for the publication in *Crystals* **2019**:

Size matters: New Zintl phase hydrides of *RE*Ga (*RE* = Y, La, Tm) and *RE*Si (*RE* = Y, Er, Tm) with large and small cations

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Figure S1. Rietveld refinement of the crystal structure of $YSiH_x$; contribution from the Apiezon grease marked with an asterisk (*); Bragg markers from top to bottom: $YSiH_x$ (84.3(2)%), YSi_2 (13.4(2)%), Y_2O_3 (2.3(1)%); $R_p = 1.80\%$, $R_{wp} = 2.89\%$, GooF = 1.16.

Table S1. Crystal structure of YSiH_x, *Cmcm*, a = 4.00947(7) Å, b = 11.6122(2) Å, c = 3.84639(4) Å. Negative *B*-values are caused by X-ray absorption.

atom	site	x	У	Z	B _{iso} /Å ²
Y	4 <i>c</i>	0	0.14470(8)	1⁄4	-0.26(2)
Si	4 <i>c</i>	0	0.4407(2)	1⁄4	0.92(6)



Figure S2. Rietveld refinement of the crystal structure of $ErSiH_x$; contribution from the Apiezon grease marked with an asterisk (*); Bragg markers from top to bottom: $ErSiH_x$ (94.41(8)%), $ErSi_2$ (4.38(6)%), Er_2O_3 (1.21(6)%); Rp = 1.45%, Rwp = 1.96%, GooF = 0.79.

Table S2. Crystal structure of ErSiH_x, *Cmcm*, a = 3.96646(5) Å, b = 11.3569(2) Å, c = 3.82155(4) Å. Negative *B*-values are caused by X-ray absorption.

atom	site	x	У	Z	$B_{\rm iso}/{\rm \AA}^2$
Er	4 <i>c</i>	0	0.14665(6)	1⁄4	-0.64(2)
Si	4 <i>c</i>	0	0.4454(2)	1⁄4	0.65(7)



Figure S3. Rietveld refinement of the crystal structure of $TmSiH_x$; contribution from the Apiezon grease marked with an asterisk (*); Bragg markers from top to bottom: $TmSiH_x$ (85.3(1)%), $TmSi_2$ (14.7(1)%); Rp = 1.78%, Rwp = 2.78%, GooF = 1.11.

Table S3. Crystal structure of TmSiH_x, *Cmcm*, *a* = 3.95185(5) Å, *b* = 11.27207(18) Å, *c* = 3.80638(4) Å.

atom	site	x	У	Z	$B_{\rm iso}/{\rm \AA}^2$
Tm	4 <i>c</i>	0	0.14629(6)	1⁄4	0.02(3)
Si	4 <i>c</i>	0	0.4438(3)	1⁄4	1.08(8)



Figure S4. Differential scanning calorimetry (DSC) of TmGa at 1 MPa hydrogen pressure; black: first run, red: second run.



Figure S5. Rietveld refinement of the crystal structure of α -YGaH_x after storage in the glove box using a triple *a* CrB superstructure, Bragg markers from top to bottom: YGaH_x (98.6(20)%), Y₂O₃ (1.3(7)%), diamond (optical dilution); *R*p = 11.13%, *R*wp = 13.90%, GooF = 1.53.

Table S4: Crystal structure of YGaH_x, *Cmcm*, a = 11.2506(4) Å, b = 12.6089(5) Å, c = 4.07088(14) Å. Negative *B*-values are caused by X-ray absorption.

atom	site	X	У	Z	B _{iso} /Å ²
Y1	4 <i>c</i>	0	0.3132(3)	1⁄4	-0.03(6)
Y2	8g	0.1774(3)	0.8596(2)	1⁄4	B _{iso} (Y1)
Ga1	4 <i>c</i>	0	0.0553(4)	1⁄4	0.39(9)
Ga2	8g	0.1338(3)	0.5542(3)	1⁄4	B _{iso} (Ga2)

 Table S5. k-point lattice for DFT calculations.

compound	k-point lattice
For structure optimization	220
LaGa, LaGaH, YGa YGa, YGaH (filled CrB	-4 4 0
structure type)	004
For DOS calculation	440
LaGa, LaGaH, YGa YGa, YGaH (filled CrB	-880
structure type)	008
For structure optimization	440
LaGaH _{1.66} ,YGaH (distorted CrB structure type)	-4 4 0
	008
For DOS calculation	880
LaGaH _{1.66} ,YGaH (distorted CrB structure type)	-880
	0016



Figure S6. Crystal structures of LaGa, LaGaH and LaGaH_{1,66} after structure optimization by quantummechanical (DFT) calculations.

Table S6. Structural parameters of LaGa derived by DFT, space group *Cmcm*, a = 4.56633 Å, b = 11.60617 Å, c = 4.23479 Å.

atom	site	x	У	Z
La	4 <i>c</i>	0	0.141242	1⁄4
Ga	4 <i>c</i>	0	0.432520	1⁄4

Table S7. Structural parameters of LaGaH derived by DFT, space group *Cmcm*, a = 4.34922 Å, b = 12.46098 Å, c = 4.27031 Å.

atom	site	x	У	Z
La	4 <i>c</i>	0	0.155103	1⁄4
Ga	4 <i>c</i>	0	0.445060	1⁄4
Н	4 <i>c</i>	0	0.751506	1⁄4

Table S8. Structural parameters of LaGaH_{1.66} derived by DFT, space group *Cmcm*, a = 12.81949 Å, b = 12.60269 Å, c = 4.27632 Å.

atom	site	X	У	Z
La	4 <i>c</i>	0	0.162490	1⁄4
La	8g	0.169767	0.645782	1⁄4
Ga	4 <i>c</i>	0	0.442616	1⁄4
Ga	8g	0.154619	0.941939	1⁄4
Н	4 <i>c</i>	0	0.743123	1⁄4
Н	8 <i>g</i>	0.198669	0.448495	1⁄4



Figure S7. Crystal structures of YGa, YGaH (simple filled CrB type structure) and YGaH (filled triple *a* CrB superstructure) after structure optimization by quantum-mechanical (DFT) calculations.

Table S9. Structural parameters of YGa derived by DFT, space group *Cmcm*, a = 4.33904 Å, b = 10.97076 Å, c = 4.06376 Å.

atom	site	x	У	Z
Y	4 <i>c</i>	0	0.139222	1⁄4
Ga	4 <i>c</i>	0	0.423142	1⁄4

Table S10. Structural parameters of YGaH (filled CrB type structure) derived by DFT, space group *Cmcm*, a = 4.06442 Å, b = 11.51407 Å, c = 4.07609 Å.

atom	site	x	У	Z
Y	4 <i>c</i>	0	0.156134	1⁄4
Ga	4 <i>c</i>	0	0.439259	1⁄4
н	4 <i>c</i>	0	0.753568	1⁄4

Table S11. Structural parameters of YGaH (distorted CrB type structure) derived by DFT, space group *Cmcm*, a = 11.14606 Å, b = 12.70683 Å, c = 4.09353 Å.

atom	site	X	У	Z
Y	4 <i>c</i>	0	0.308628	1⁄4
Y	8g	0.179039	0.859671	1⁄4
Ga	4 <i>c</i>	0	0.055996	1⁄4
Ga	8g	0.129239	0.557599	1⁄4
н	4 <i>c</i>	0	0.753568	1⁄4
н	8g	0.177123	0.235322	1⁄4